

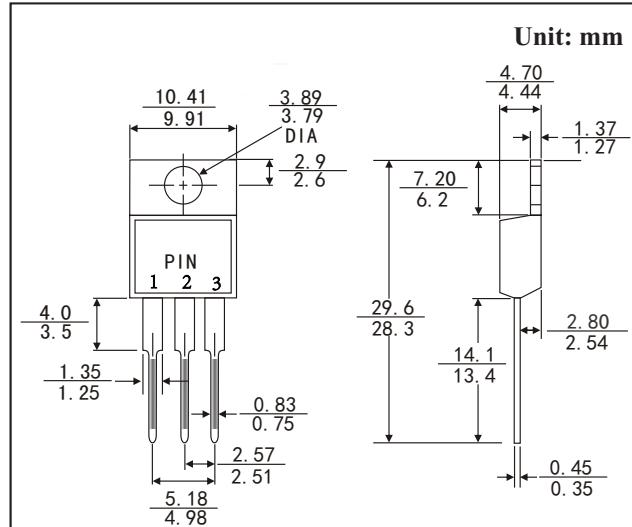
TO-220AB Plastic-Encapsulate Transistors

FEATURES

- Ultra Low Forward Voltage Drop
- Excellent High Temperature Stability
- Patented Super Barrier Rectifier Technology
- Soft, Fast Switching Capability
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0

MECHANICAL DATA

- Case: TO-220AB molded plastic body
- Terminals: Matte Tin Finish annealed over Copper leadframe Solderable per MIL-STD-202, Method 208



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

PARAMETER	SYMBOL	VALUE	UNIT
Maximum repetitive peak reverse voltage	V _{RRM}	100	V
Maximum rms voltage	V _{RMS}	70	V
Maximum average forward rectified current per device per diode	I _{F(AV)}	40 20	A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load	I _{FSM}	300	A
Typical thermal resistance per diode (Note 1)	R _{θJC}	2	°C/W
Operating junction temperature range	T _J	-55 to + 150	°C
Storage temperature range	T _{STG}	-55 to + 150	°C

Note : 1. Mounted on infinite heatsink.

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Breakdown voltage per diode	V _{BR}	I _R =0.5mA	100	-	-	V
Instantaneous forward voltage per diode	V _F	I _F =5A I _F =10A I _F =20A T _J =25°C	-	0.46	-	V
		-	-	0.55	-	
		-	-	0.65	0.70	
	I _R	I _F =5A I _F =10A I _F =20A T _J =125°C	-	0.38	-	V
		-	-	0.50	-	
		-	-	0.55	-	
Reverse current per diode	I _R	V _R =70V	-	5 6	-	µA mA
		V _R =100V T _J =25°C T _J =125°C	-	-	100 - 12	µA mA

RATINGS AND CHARACTERISTIC CURVES

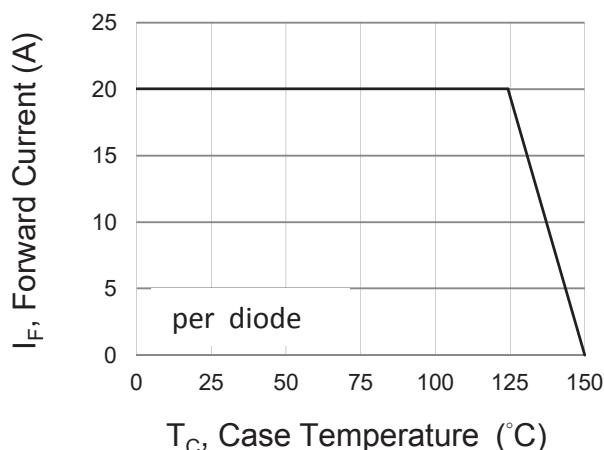


Fig.1 Forward Current Derating Curve

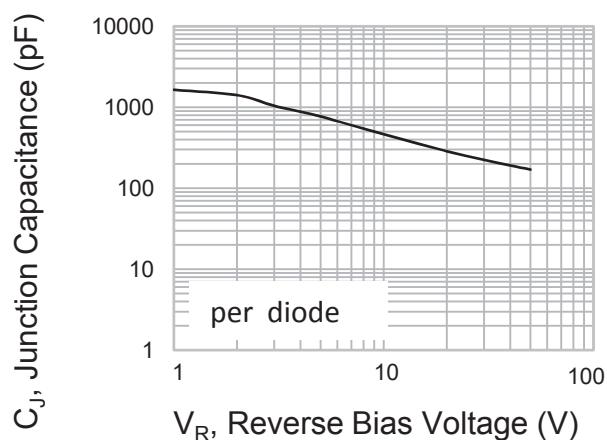


Fig.2 Typical Junction Capacitance

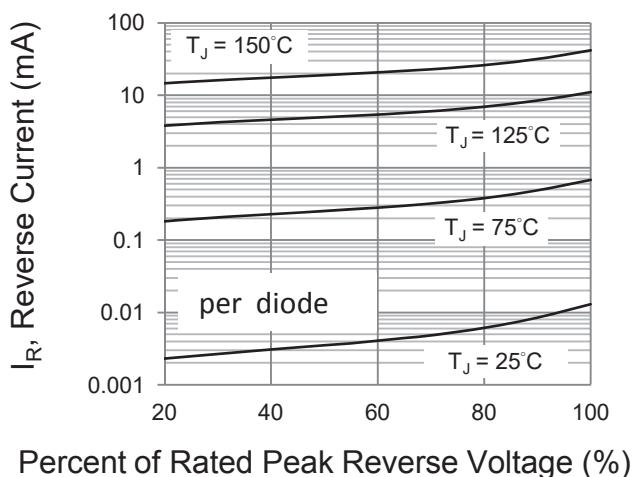


Fig.3 Typical Reverse Characteristics

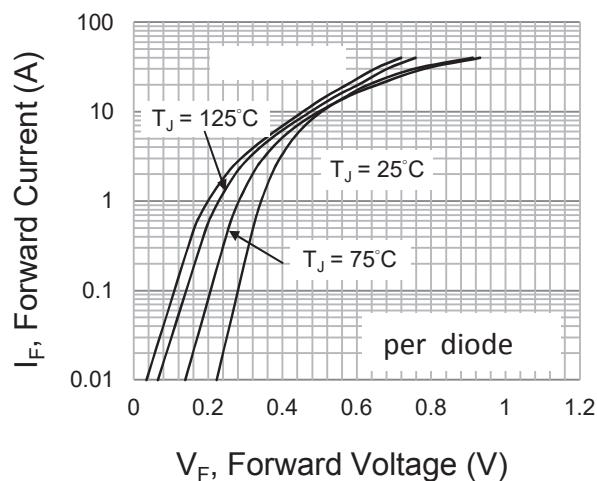


Fig.4 Typical Forward Characteristics